**Product data sheet** 

## **Product profile**

### 1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD59 (2-lead TO-220AC) plastic package.

### 1.2 Features

- Extremely fast switching
- Reduces switching loss in associated **MOSFET**
- Low thermal resistance
- Low reverse recovery current

### 1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies
- Half-bridge lighting ballasts
- Factor Correction (PFC)

#### 1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- $V_F = 1.32 \text{ V (typ)}$

- $I_{F(AV)} \le 15 A$
- $t_{rr} = 19 \text{ ns (typ)}$

## **Pinning information**

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k — <b>↓</b> a 001aaa020
mb	mounting base; cathode	1 2	
		SOD59 (2-lead TO-220)	AC)



# 3. Ordering information

### Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BYC15-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

## 4. Limiting values

### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	square waveform; $\delta$ = 1.0; $T_{mb} \le 100$ °C	-	500	V
I <sub>F(AV)</sub>	average forward current	square waveform; $\delta$ = 0.5; $T_{mb} \leq 98~^{\circ}C$	-	15	Α
I <sub>FRM</sub>	repetitive peak forward current	square waveform; $\delta$ = 0.5; $T_{mb} \leq$ 98 °C; $t_p$ = 25 $\mu s$	-	30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform	-	200	Α
		t = 8.3 ms; sinusoidal waveform	-	220	Α
T <sub>stg</sub>	storage temperature		-40	+150	°C
Tį	junction temperature		-	150	°C

## 5. Thermal characteristics

### Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; see Figure 1	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

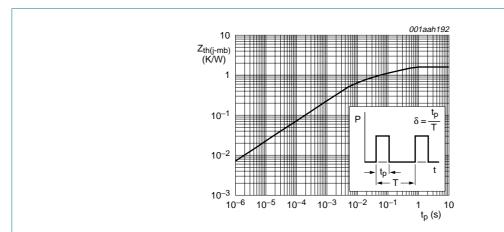


Fig 1. Transient thermal impedance from junction to mounting base as a function of pulse width

## 6. Characteristics

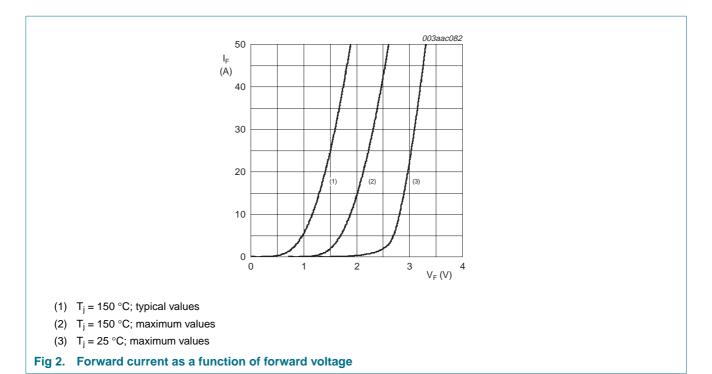
**Table 5. Characteristics** 

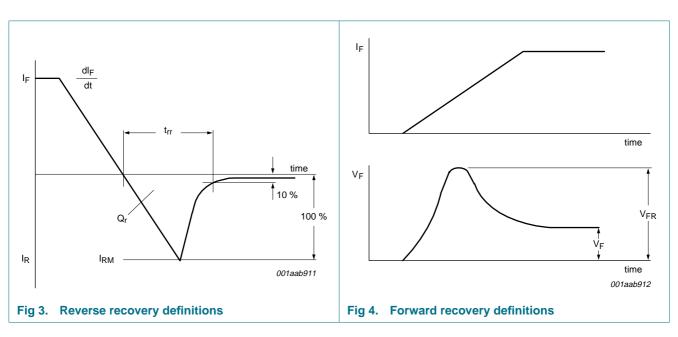
 $T_j = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
V <sub>F</sub>	forward voltage	$I_F = 15 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{}$	-	1.32	2.03	V
		$I_F = 30 \text{ A}$ ; $T_j = 150 ^{\circ}\text{C}$ ; see Figure 2	-	1.64	2.34	V
		I <sub>F</sub> = 15 A; see <u>Figure 2</u>	-	1.89	2.9	V
$I_R$	reverse current	V <sub>R</sub> = 600 V	-	12	200	μΑ
		$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.1	3.0	mA
Dynamic c	haracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A to $V_R$ = 30 V; $dI_F/dt$ = 50 A/ $\mu$ s; see Figure 3	-	35	55	ns
		$I_F$ = 15 A to $V_R$ = 400 V; $dI_F/dt$ = 500 A/ $\mu$ s; see Figure 3				
		T <sub>j</sub> = 25 °C	-	19	-	ns
		T <sub>j</sub> = 100 °C	-	32	40	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F$ = 15 A to $V_R$ = 400 V; $T_j$ = 125 °C; see Figure 3				
		$dI_F/dt = 50 A/\mu s$	-	3.0	7.5	Α
		$dI_F/dt = 500 A/\mu s$	-	9.5	12	Α
$V_{FR}$	forward recovery voltage	$I_F = 15 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; see Figure 4	-	8	11	V

**BYC15-600** 

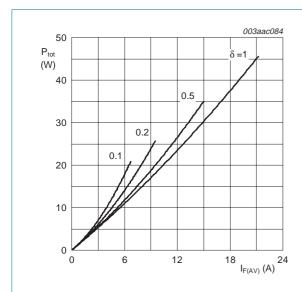
Rectifier diode, hyperfast





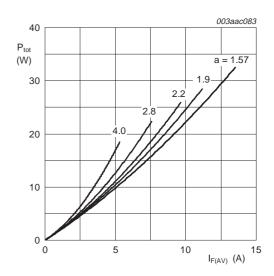
NXP Semiconductors BYC15-600

## Rectifier diode, hyperfast



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ 

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form \ factor = I_{F(RMS)} \ / \ I_{F(AV)}$ 

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

## **Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC

SOD59

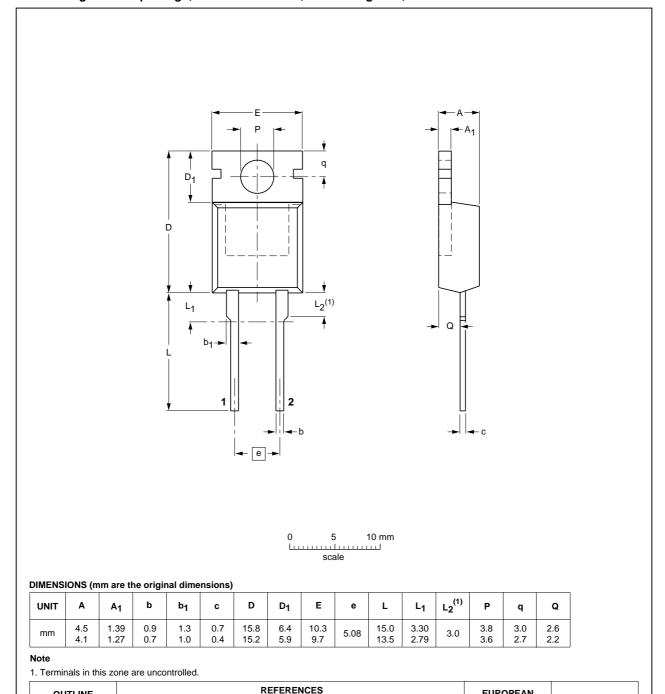


Fig 7. Package outline SOD59 (2-lead TO-220AC)

IEC

OUTLINE

VERSION

SOD59

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**JEITA** 

**EUROPEAN** 

**PROJECTION** 

**ISSUE DATE** 

99-09-13

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**JEDEC** 

2-lead TO-220AC

**BYC15-600** 

Rectifier diode, hyperfast

# 8. Revision history

### Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC15-600_1	20071129	Product data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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**BYC15-600** 

### Rectifier diode, hyperfast

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